

9/ 1995. The entire disclosures of the above applications are hereby incorporated by reference. --

**IN THE CLAIMS:**

Please cancel all of the claims, i.e., claims 1-24, without prejudice and substitute therefore the following new claims 25-65:

-- 25. A process for fabricating a semiconductor device, comprising the step of:

bonding a semiconductor device to a support with an organic die-bonding film at conditions of temperature of 100-250°C and pressure of 0.1-30 gf/mm<sup>2</sup> to produce a bonded chip wherein the organic die-bonding film has a peel strength of 0.5 kgf/(5 mm x 5mm chip) or higher.

26. A process according to claim 25, further comprising the step of: encapsulating the bonded chip to produce the semiconductor device.

27. A process according to claim 25, wherein said step of bonding comprises bonding with an organic die-bonding film having a modulus of elasticity of 10 Mpa or less at a temperature of 250°C.

28. A process according to claim 27, wherein said step of bonding comprises bonding with an organic die-bonding film further having a water absorption of 1.5% by volume or less.